

ABSTRACT

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A technique of detecting an abnormality in measuring of a film thickness of a workpiece, such as a wafer, is disclosed. A method includes: generating multiple spectra of reflected light from multiple measurement points on a workpiece over a predetermined
10 period of time during polishing of the workpiece; classifying the multiple spectra into a plurality of groups including at least a first group and a second group according to feature of each of the multiple spectra; determining a monitoring index value based on at least the number of spectra included in the first group; and detecting an abnormality in measuring of the film thickness of the at least one workpiece based on comparison of the monitoring index
15 value with a threshold value.

FIG. 10